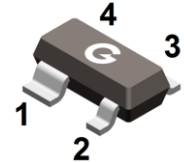
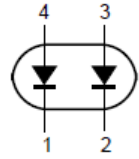




BAS56 High-speed Double Diode

FEATURES

- High switching speed
- Continuous reverse voltage
- Repetitive peak reverse voltage
- Repetitive peak forward current



APPLICATIONS

- High speed switching in e.g. surface mounted circuits

Marking : L51

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MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	60	V
Repetitive Peak Reverse Voltage series connection	V_{RRM}	120	V
Continuous Reverse Voltage	V_R	60	V
Continuous Reverse Voltage series connection	V_R	120	V
Continuous Forward Current Single diode loaded(Note1) Double diode loaded(Note1)	I_F	200 150	mA
Repetitive peak forward current Single diode loaded Double diode loaded	I_{FSM}	600 430	mA
Non-repetitive peak forward current Square wave, $T_j=25^\circ\text{C}$ prior to surge t=1us t=100us t=10ms	I_{FSM}	9 3 1.7	A
Total Power Dissipation	P_d	250	mW
Storage and Junction Temperature Range	$T_{STG} T_j$	-65 to +150	°C

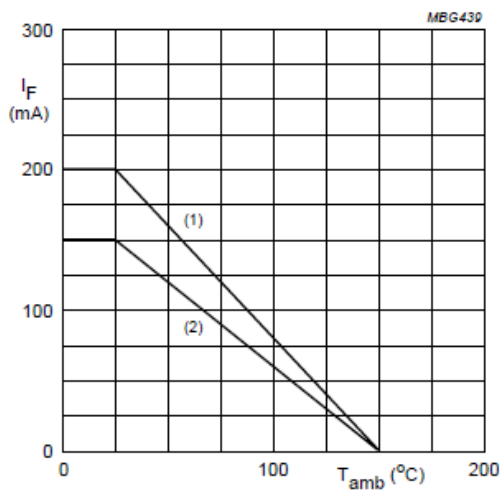
Note:1.Device mounted on an FR4 printed-circuit board.



ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Min	MAX	UNIT	Test Condition
Reverse Leakage Current	I_R	-	100	nA	$V_R=60V$
			100	μA	$V_R=60V, T_j=150^\circ C$
			100	nA	$V_R=120V$
			100	μA	$V_R=120V, T_j=150^\circ C$
Forward voltage	V_F	-	1	V	$I_F=200mA$
Diode Capacitance	C_D	-	2.5	pF	$V_R=0V, f=1.0MHz$
Reverse Recovery Time	t_{rr}	-	6	ns	$I_F=I_R=400mA,$ $R_L=100\Omega$ $I_{rr}=0.1 \cdot I_R$
Forward recovery voltage	V_{fr}	-	2.0		$I_F=400mA, t_r=30ns$
			1.5		$I_F=400mA, t_r=100ns$

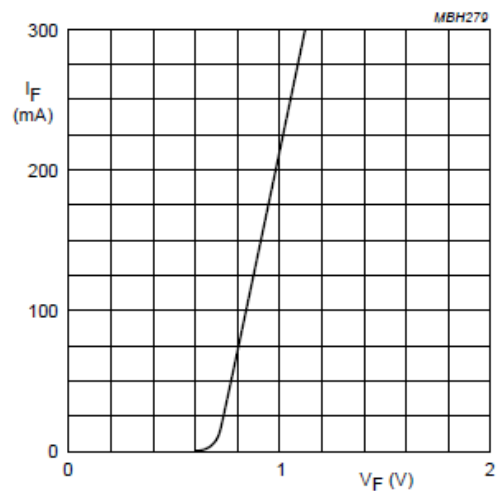
TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Device mounted on a FR4 printed-circuit board.

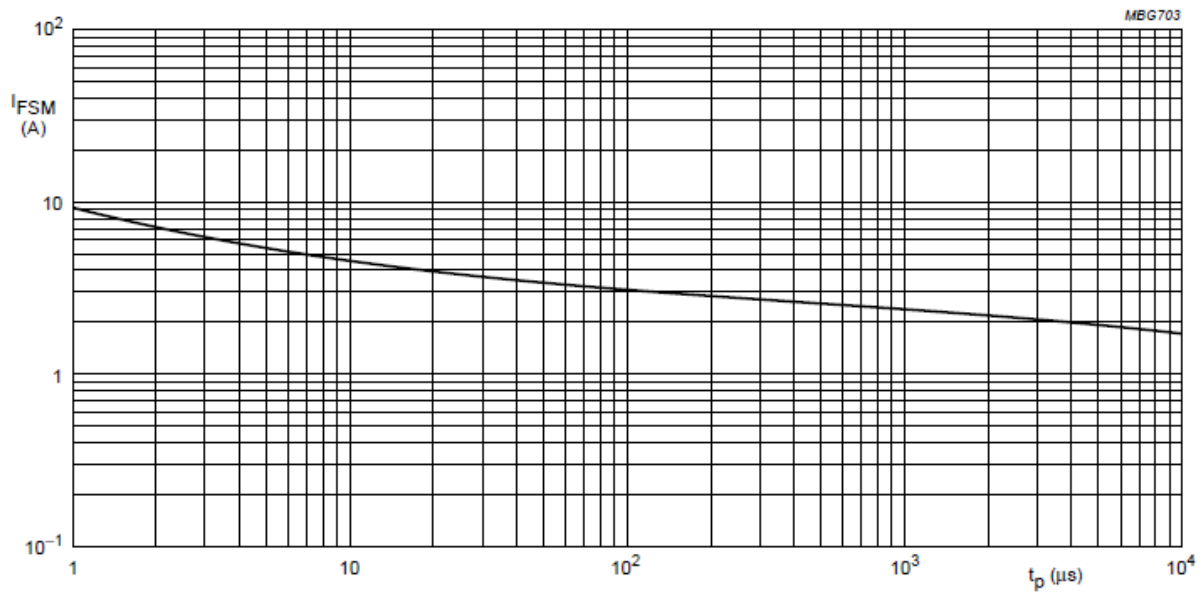
- (1) Single diode loaded.
- (2) Double diode loaded.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



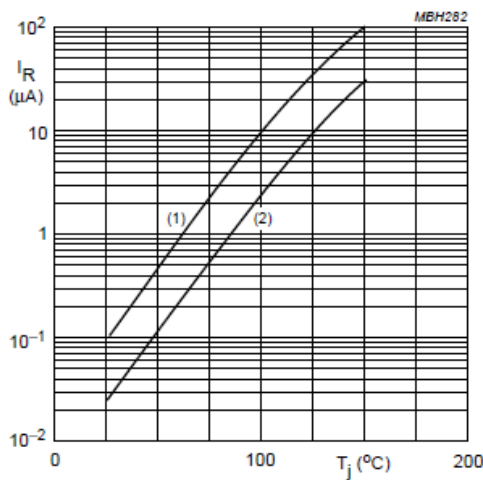
$T_j = 25^\circ C.$

Fig.3 Forward current as a function of forward voltage; typical values.



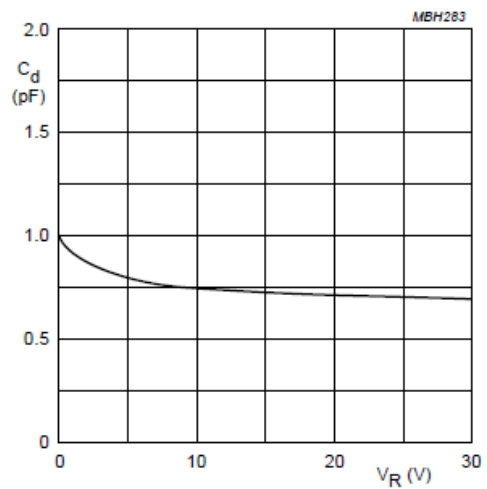
Based on square wave currents.
 $T_j = 25\text{ }^\circ\text{C}$ prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



(1) $V_R = 60\text{ V}$; maximum values.
 (2) $V_R = 60\text{ V}$; typical values.

Fig.5 Reverse current as a function of junction temperature.



$f = 1\text{ MHz}$; $T_j = 25\text{ }^\circ\text{C}$.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



Package Outline

Plastic surface mounted package

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